

introducing processing gas comprising a gas comprising nitrogen atoms
and a gas comprising hydrogen atoms into the process chamber;
etching the organic film; and
stopping the etching before the etching goes through the organic film.

7. (New) A method of etching according to claim 6, wherein the gas comprising nitrogen atoms constitute N_2 and the gas comprising hydrogen atoms constitute H_2 .
8. (New) A method of etching according to claim 6, wherein the processing gas further comprises Ar.
9. (New) A method of etching according to claim 7, wherein the processing gas further comprises Ar.
10. (New) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:
 - placing the workpiece in a hermetically sealed process chamber;
 - introducing processing gas into the process chamber;
 - pressurizing the process chamber to a pressure equal to or higher than 500 mTorr;
 - etching the organic film; and
 - stopping the etching before the etching goes through the organic film.
11. (New) A method of etching according to claim 10, wherein the processing gas comprises a gas comprising nitrogen atoms and a gas comprising hydrogen atoms.

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12. (New) A method of etching an organic film on a workpiece, the organic film having an etching mask, the method comprising:
- placing the workpiece in a hermetically sealed process chamber;
 - introducing processing gas comprising a gas comprising nitrogen atoms and a gas comprising hydrogen atoms into the process chamber;
 - pressurizing the process chamber to a pressure between 500 - 800 mTorr;
 - etching the organic film; and
 - stopping the etching before the etching goes through the organic film.
13. (New) A method of etching according to claim 12, wherein the gas comprising nitrogen atoms constitute N_2 and the gas comprising hydrogen atoms constitute H_2 .
14. (New) A method of etching according to claim 12, wherein the processing gas further comprises Ar.
15. (New) A method of etching according to claim 13, wherein the processing gas further comprises Ar.

IN THE DRAWINGS:

Subject to the approval of the Examiner, please amend the drawings as set forth in the Request for Approval of Drawing Changes submitted herewith.

REMARKS

Applicants respectfully request that this Preliminary Amendment be entered prior to the examination of the application. Applicant respectfully requests favorable consideration of this application.

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